

Supporting information

Insighting Excellent Persistent Luminescence and Detecting Trap Distribution in BaHfSi₃O₉:Eu²⁺,Pr³⁺

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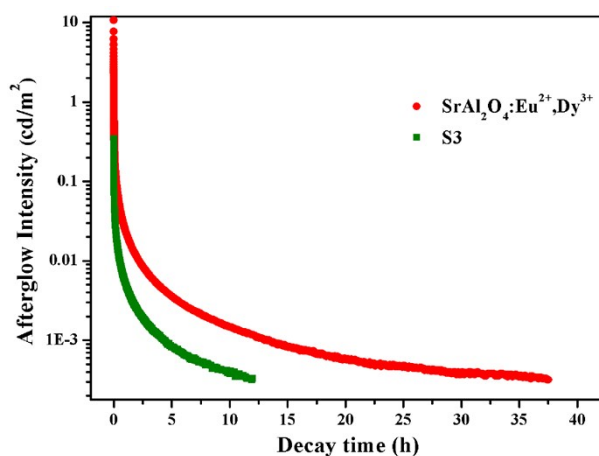


Fig. S1 Persistent decay curves of the S3 sample and SrAl₂O₄:Eu²⁺,Dy³⁺.

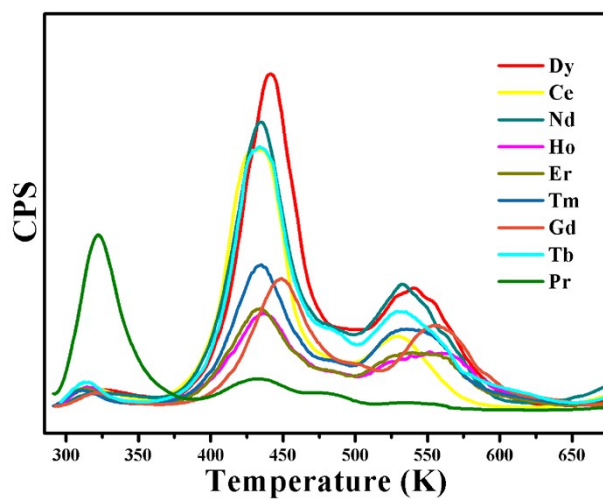


Fig. S2 The TL spectra of BaHfSi₃O₉:Eu²⁺,R³⁺ (R=Dy, Ce, Nd, Ho, Er, Tm, Gd, Tb, Pr).

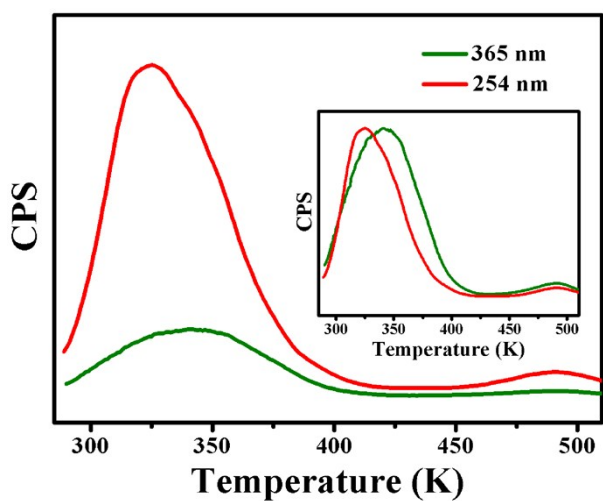


Fig. S3 TL glow curves of the S3 sample recorded after 254 nm or 365 nm lights excitation for 30 s.